

Accepted Manuscript

Large field-induced strain, giant strain memory effect, and high thermal stability energy storage in (Pb,La)(Zr,Sn,Ti)O₃ antiferroelectric single crystal

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PII: S1359-6454(18)30052-1

DOI: [10.1016/j.actamat.2018.01.021](https://doi.org/10.1016/j.actamat.2018.01.021)

Reference: AM 14315

To appear in: *Acta Materialia*

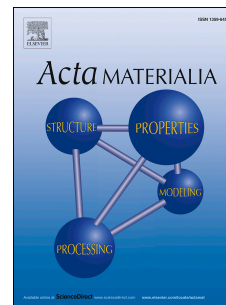
Received Date: 27 November 2017

Revised Date: 10 January 2018

Accepted Date: 12 January 2018

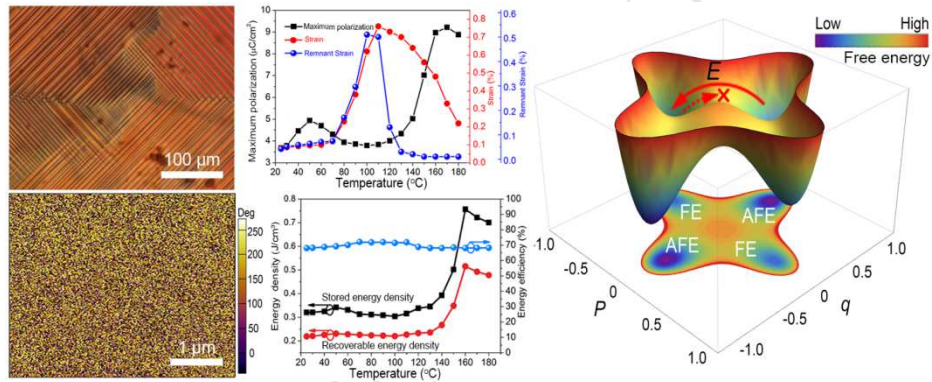
Please cite this article as: F. Zhuo, Q. Li, Y. Zhou, Y. Ji, Q. Yan, Y. Zhang, X. Xi, X. Chu, W. Cao, Large field-induced strain, giant strain memory effect, and high thermal stability energy storage in (Pb,La)(Zr,Sn,Ti)O₃ antiferroelectric single crystal, *Acta Materialia* (2018), doi: 10.1016/j.actamat.2018.01.021.

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Graphical abstract

A large field-induced strain value of 0.76%, a giant strain memory effect of 0.51%, and a good thermal stability of energy storage performance with the recoverable energy variation less than 5% in a wide temperature range were achieved in the $(\text{Pb},\text{La})(\text{Zr},\text{Sn},\text{Ti})\text{O}_3$ tetragonal antiferroelectric single crystals grown by the conventional flux method.



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